

### SSC8428GS6

### **N-Channel Enhancement Mode MOSFET**

#### Features

V <sub>DS</sub>	V <sub>GS</sub>	R <sub>DS(ON)</sub> Typ.	ID
		14mΩ@10V	
20V	±12V	16mΩ@4V5	7A
		20mΩ@2V5	

### Description

This SSC8428GS6 combines advanced trench MOSFET technology with a low resistance package to provide extremely low RDSON. This device is ideal for load switch and battery protection applications.

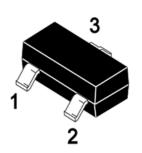
## Applications

- Load Switch
- Battery Isolation

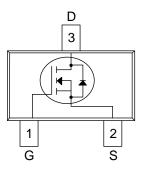
### > Ordering Information

Device	Package	Shipping		
SSC8428GS6	SOT-23	3000/Reel		

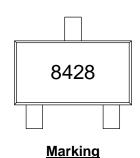
## Pin configuration



**SOT-23** 



Pin Configuration (Top View)



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### ➤ Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Ratings	Unit	
V <sub>DSS</sub>	Drain-to-Source Voltage		20	V
V <sub>GSS</sub>	Gate-to-Source Voltage		±12	V
ID	Continuous Drain Current a		7	А
I <sub>DM</sub>	Pulsed Drain Current <sup>b</sup>		30	А
P <sub>D</sub>	Power Dissipation <sup>c</sup>	Tc = 25°C	1.2	W
P <sub>DSM</sub>	Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25°C	0.65	W
TJ	Operation junction temperature		-55~150	$^{\circ}$ C
T <sub>STG</sub>	Storage temperature range		-55~150	$^{\circ}\!\mathbb{C}$

### ➤ Thermal Resistance Ratings (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Maximum	Unit	
Reja	Junction-to-Ambient Thermal Resistance a	200	°C AA/	
R <sub>θ</sub> JC	Junction-to-Case Thermal Resistance	105	- °C/W	

### Note:

- a. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper, in a still air environment with T<sub>A</sub>=25 °C. The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.
- b. Repetitive rating, pulse width limited by junction temperature.
- c. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

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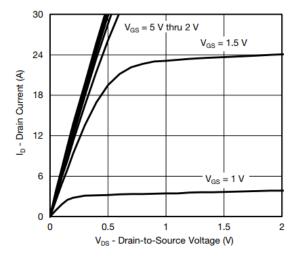


# $\succ$ Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

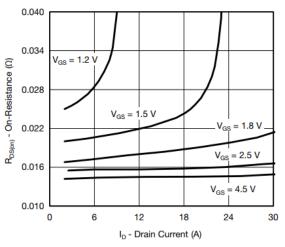
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	20			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250uA	0.5	0.7	1	V
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 4.5A		14	18	mΩ
Drain-Source On-Resistance		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.5A		16	21	
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2.5A		20	27	
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V			1	μA
Gate-Source Leak Current	Igss	$V_{GS} = \pm 12V, V_{DS} = 0V$			±100	nA
Transconductance	G <sub>FS</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 4.5A		8		S
Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 0.5A			1.3	V
Input Capacitance	Cıss	V 0V V 0V		600		
Output Capacitance	Coss	$V_{DS} = 8V$ , $V_{GS} = 0V$ , $f = 1MHz$		330		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	I = IIVIDZ		140		
Turn-on Delay Time	T <sub>D(ON)</sub>	V 45V D 400		7		
Rise Time	Tr	$V_{GEN}=4.5V,R_L=10\Omega$ $V_{DS}=10V,R_G=6\Omega$ $I_D=1A$		13		ns
Turn-off Delay Time	$T_{D(OFF)}$			48		
Fall Time	Tf			22		
Total Gate Charge	Q <sub>G</sub>	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V,		8.5		nC
Gate to Source Charge	Q <sub>GS</sub>			1.8		
Gate to Drain Charge	Q <sub>GD</sub>	I <sub>D</sub> = 4A		2.2		



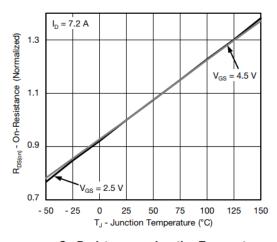
## > Typical Performance Characteristics (T<sub>A</sub>=25℃ unless otherwise noted)



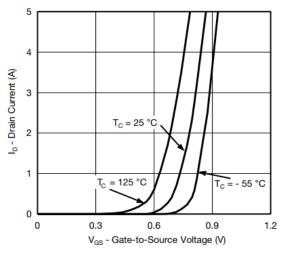
**Output Characteristics** 



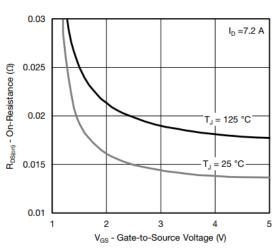
On-Resistance vs. Drain Current and Gate Voltage



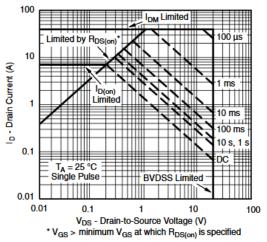
On-Resistance vs. Junction Temperature



**Transfer Characteristics** 



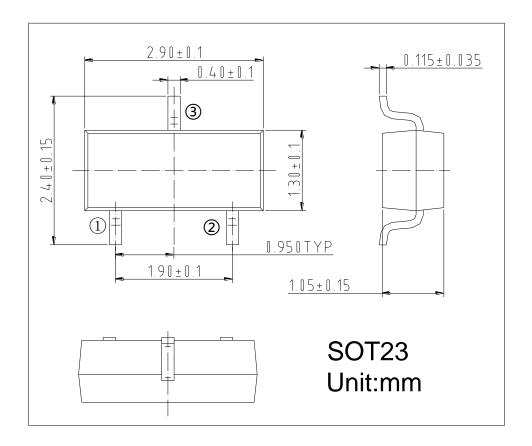
On-Resistance vs. Gate-to-Source Voltage



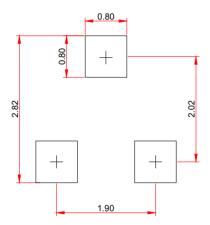
Safe Operating Area, Junction-to-Ambient



## > Package Information



## Recommended Pad outline (Unit: mm)





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